

SANYO	No.3329	2SC4458
		NPN Triple Diffused Planar Silicon Transistor
Switching Regulator Applications		

Features

- High breakdown voltage, high reliability
- Fast switching speed
- Wide ASO
- Adoption of MBIT process
- Micaless package facilitating mounting

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V _{CB0}	800	V
Collector-to-Emitter Voltage	V _{CEO}	500	V
Emitter-to-Base Voltage	V _{EBO}	7	V
Collector Current	I _C	7	A
Peak Collector Current	i _{cp}	PW ≤ 300 μs, duty cycle ≤ 10%	14 A
Base Current	I _B	3	A
Collector Dissipation	P _C	3	W
		T _c = 25°C	45 W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

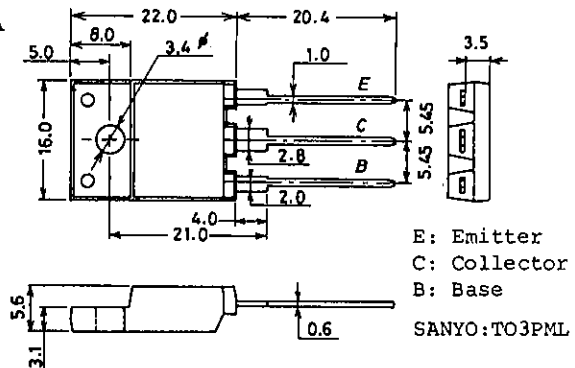
			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 500V, I _E = 0			10	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V, I _C = 0			10	μA
DC Current Gain	h _{FE(1)}	V _{CE} = 5V, I _C = 0.6A	15※		50※	
	h _{FE(2)}	V _{CE} = 5V, I _C = 3A	8			
Gain-Bandwidth Product	f _T	V _{CE} = 10V, I _C = 0.6A		18		MHz
Output Capacitance	c _{ob}	V _{CB} = 10V, f = 1MHz		80		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = 3A, I _B = 0.6A			1	V
B-E Saturation Voltage	V _{BE(sat)}	I _C = 3A, I _B = 0.6A			1.5	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = 1mA, I _E = 0	800			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = 5mA, R _{BE} = ∞	500			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = 1mA, I _C = 0	7			V
C-E Sustain Voltage	V _{CEX(sus)}	I _C = 2.5A, I _{B1} = -I _{B2} = 1A, L = 1mH, clamped	500			V

Continued on next page.

※ : For the h_{FE(1)} of the 2SC4458, specify two ranks or more in principle.

15 L 30	20 M 40	30 N 50
---------	---------	---------

Package Dimensions 2039A
(unit : mm)

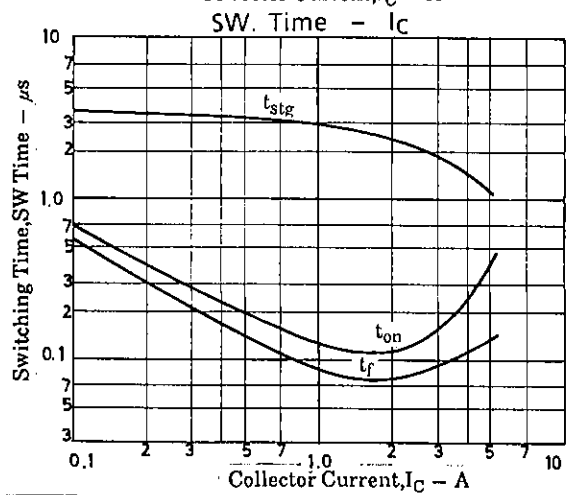
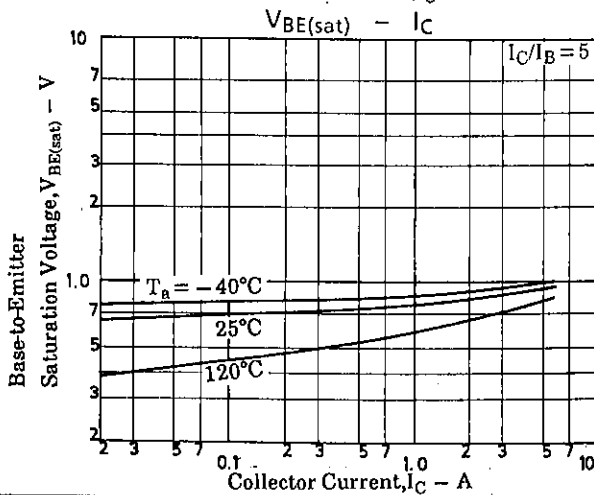
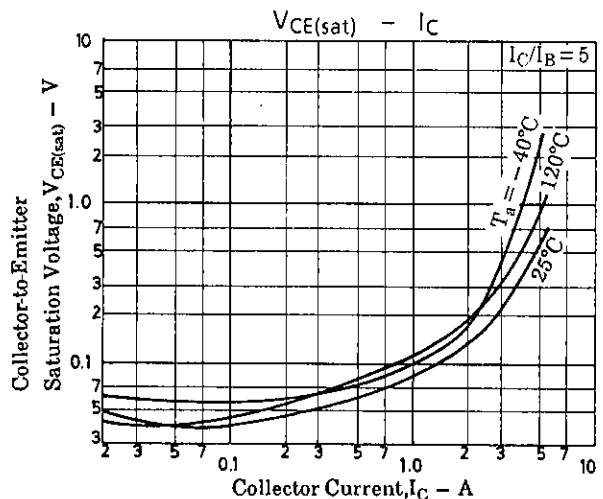
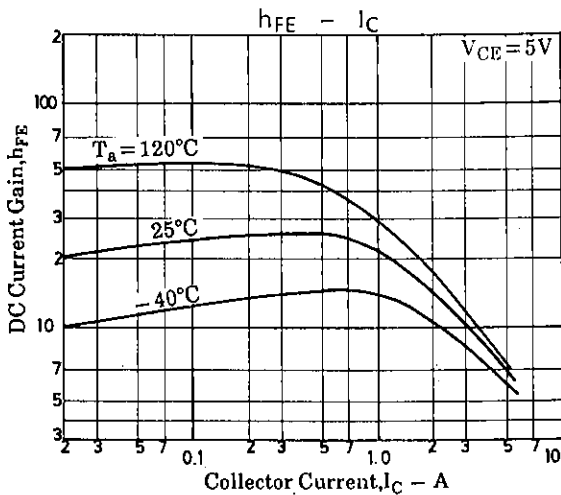
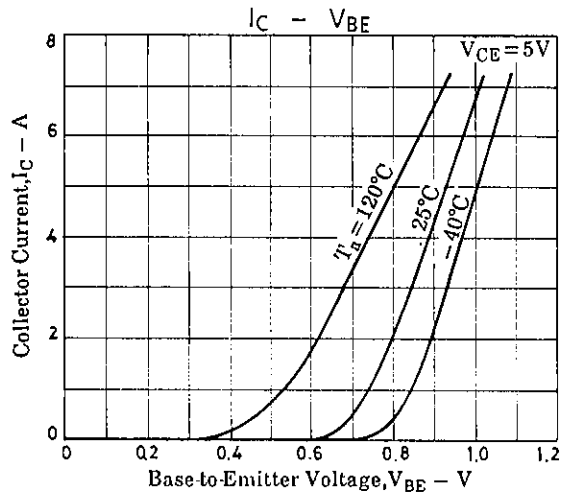
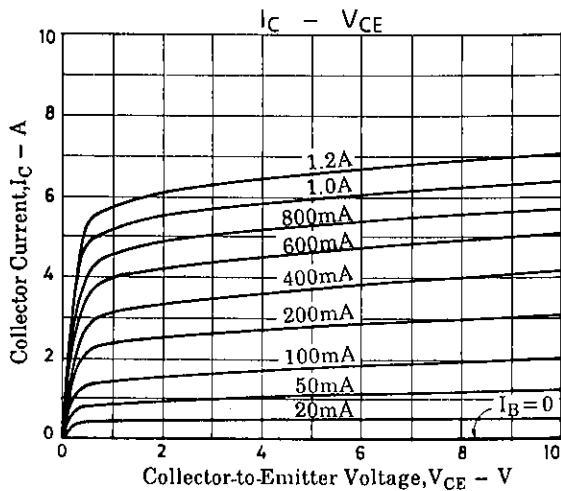
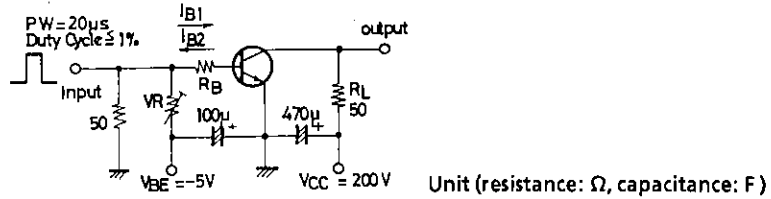


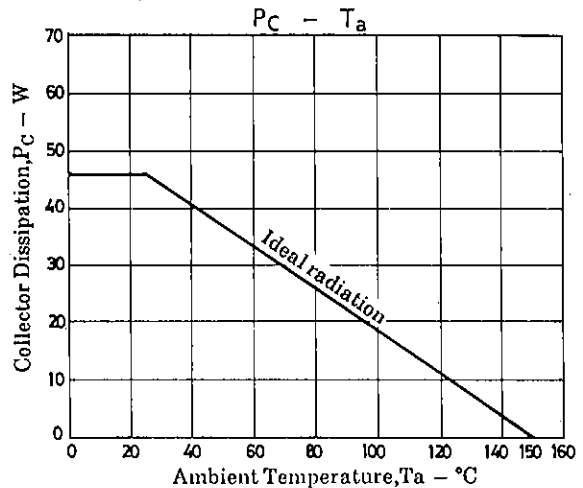
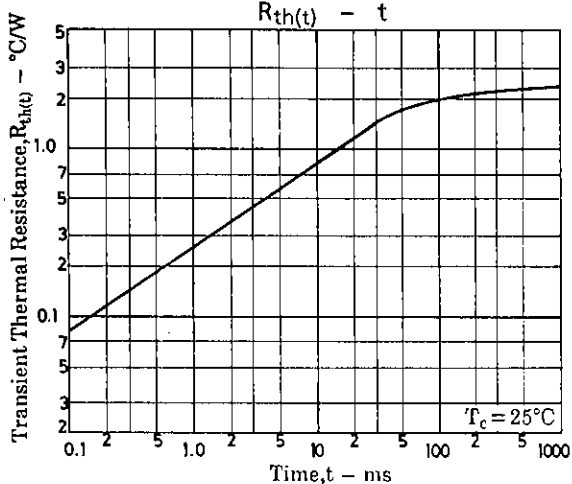
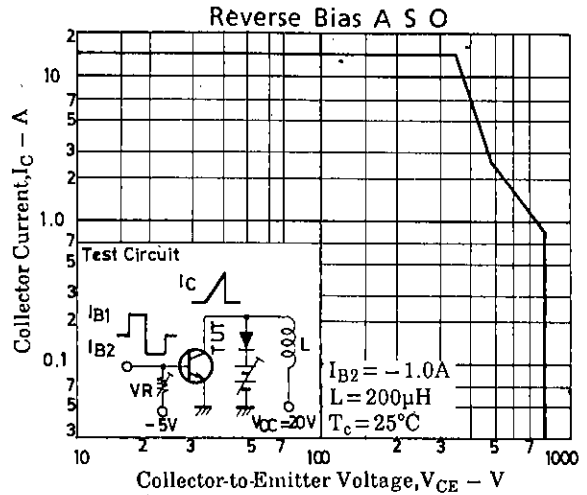
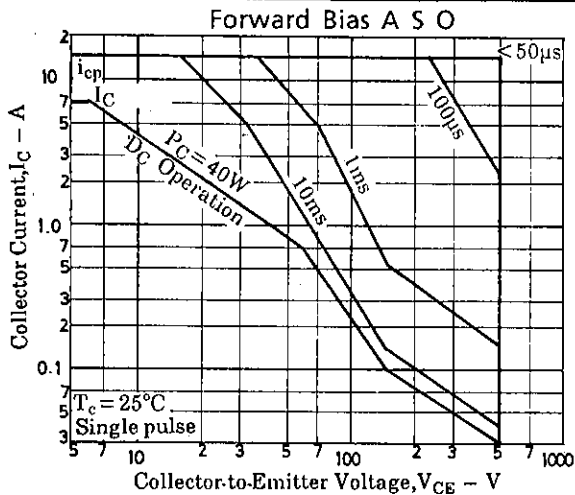
2SC4458

Continued from preceding page.

			min	typ	max	unit
Turn-ON time	t_{on}	$V_{CC} = 200V,$ $5I_{B1} = -2.5I_{B2} = I_C = 4A,$ $R_L = 50\Omega$			0.5	μs
Storage Time	t_{stg}				3.0	μs
Fall Time	t_f				0.3	μs

Switching Time Test Circuit





- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use;
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.